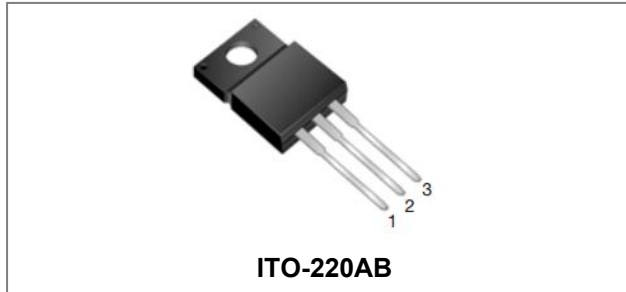


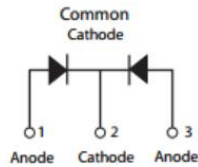
## MURF1030CT(CTR) ULTRAFAST RECTIFIER



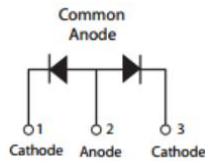
### Features

- Ultra-Fast Switching
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-0
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



MURF1030CT



MURF1030CTR

### Applications

- Switching Power Supply
- Power Switching Circuits
- General Purpose

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	$V_{RRM}$	-	300	V
Working Peak Reverse Voltage	$V_{RWM}$			
DC Blocking Voltage	$V_R$			
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_c=100^\circ\text{C}$ , rectangular wave form	5(Per Leg) 10(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	$I_{FSM}$	8.3ms, Half Sine pulse	150	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop(Per Leg)*	$V_{F1}$	@5A, Pulse, $T_J = 25^\circ\text{C}$	0.95	1.3	V
	$V_{F2}$	@5A, Pulse, $T_J = 125^\circ\text{C}$	0.85	1.2	V
Reverse Current(Per Leg)*	$I_{R1}$	@ $V_R = \text{rated } V_R, T_J = 25^\circ\text{C}$	0.02	10	$\mu\text{A}$
	$I_{R2}$	@ $V_R = \text{rated } V_R, T_J = 100^\circ\text{C}$	-	400	$\mu\text{A}$
Reverse Recovery Time(Per Leg)	$t_{rr}$	$I_F=500\text{mA}, I_R=1\text{A}, \text{ and } I_{m}=250\text{mA}$	42	50	ns
RSM Isolation Voltage ( $t=1.0$ second, R.H.<=30%, $T_A=25^\circ\text{C}$ )	$V_{iso}$	Clip mouting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	-	4500	V
		Clip mouting, the epoxy body is inside the heatsink	-	3500	
		Screw mounting, the epoxy body is inside the heatsink	-	1500	

\* Pulse width < 300  $\mu\text{s}$ , duty cycle < 2%

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**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\text{thJC}}$	DC operation	3.5	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

**Ratings and Characteristics Curves**

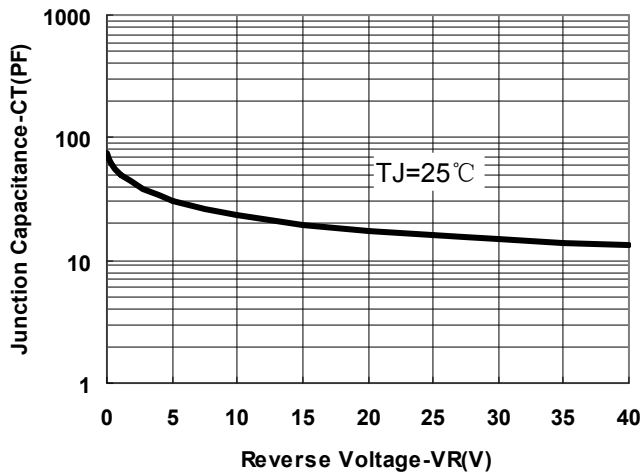


Fig.1-Typical Junction Capacitance

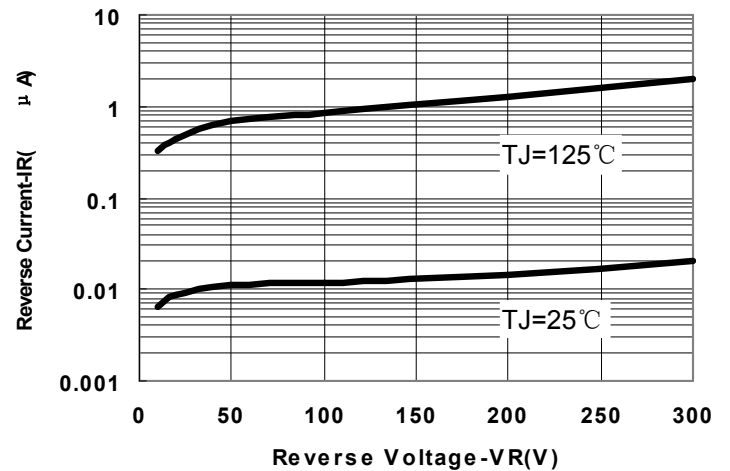


Fig.2-Typical Reverse Characteristics

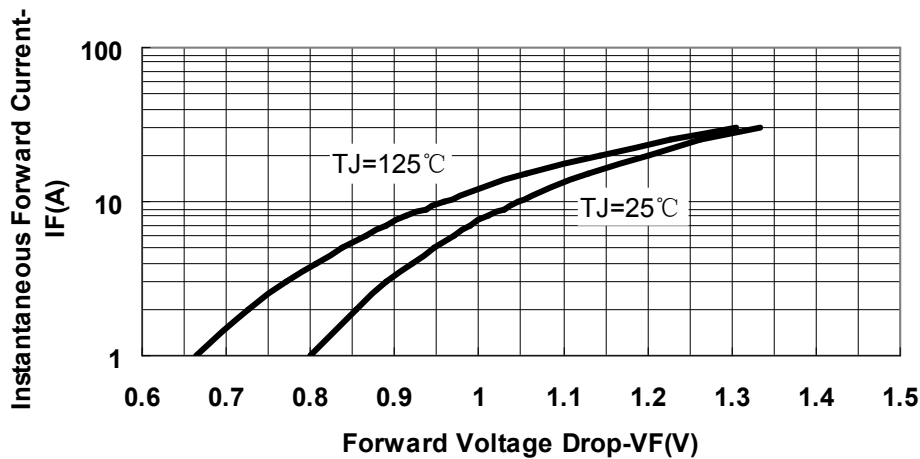
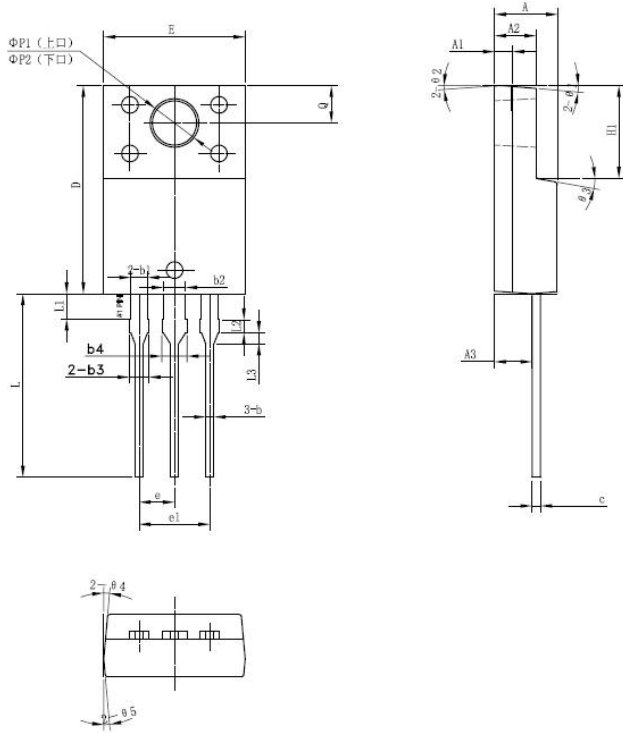


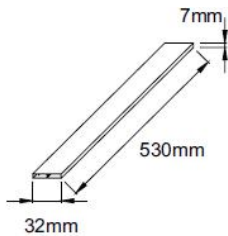
Fig.3-Typical Instantaneous Forward Characteristics

## Mechanical Dimensions ITO-220AB



SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.50	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上□)	3.30	3.50	3.70
ΦP2(下□)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

## Tube Specification

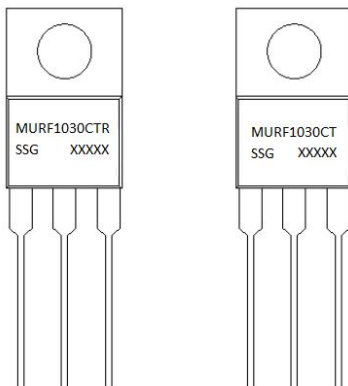


## Ordering Information

Device	Package	Shipping
MURF1030CT(CTR)	ITO-220AB (Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## Marking Diagram



Where XXXXX is YYWWL

MUR = Device Type  
 F = Package type  
 10 = Forward Current (10A)  
 30 = Reverse Voltage (300V)  
 CT(CTR) = Configuration  
 SSG = SSG  
 YY = Year  
 WW = Week  
 L = Lot Number

**Cautions:** Molding resin  
 Epoxy resin UL:94V-0

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